

General Description

The HSS2N15 is the high cell density trench N-ch MOSFETs, which provides excellent $R_{DS(on)}$ and efficiency for most of the small power switching and load switch applications.

The HSS2N15 meet the RoHS and Green Product requirement with full function reliability approved.

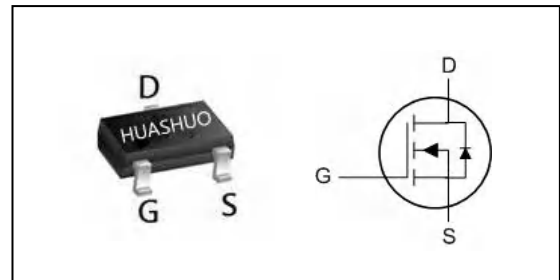
Product Summary

V_{DS}	150	V
$R_{DS(ON),max}$	280	m Ω
I_D	1.8	A

Features

- Green Device Available
- Super Low Gate Charge
- Excellent C_{dv}/dt effect decline
- Advanced high cell density Trench Technology

SOT-23L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	150	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	1.8	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	1.4	A
I_{DM}	Pulsed Drain Current ²	7.2	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ³	1.3	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	100	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	80	$^\circ\text{C}/\text{W}$



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	150	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=2A$	---	240	280	m Ω
		$V_{GS}=4.5V$, $I_D=1A$	---	250	300	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.0	2	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=150V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=150V$, $V_{GS}=0V$, $T_J=125^\circ\text{C}$	---	---	30	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
Q_g	Total Gate Charge (10V)	$V_{DS}=75V$, $V_{GS}=10V$, $I_D=2A$	---	18	---	nC
Q_{gs}	Gate-Source Charge		---	4.6	---	
Q_{gd}	Gate-Drain Charge		---	5.7	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=75V$, $V_{GS}=10V$, $R_G=6\Omega$ $I_D=2A$	---	13	---	ns
T_r	Rise Time		---	19	---	
$T_{d(off)}$	Turn-Off Delay Time		---	26	---	
T_f	Fall Time		---	9	---	
C_{iss}	Input Capacitance	$V_{DS}=75V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	840	---	pF
C_{oss}	Output Capacitance		---	119	---	
C_{rss}	Reverse Transfer Capacitance		---	25	---	

Diode Characteristics

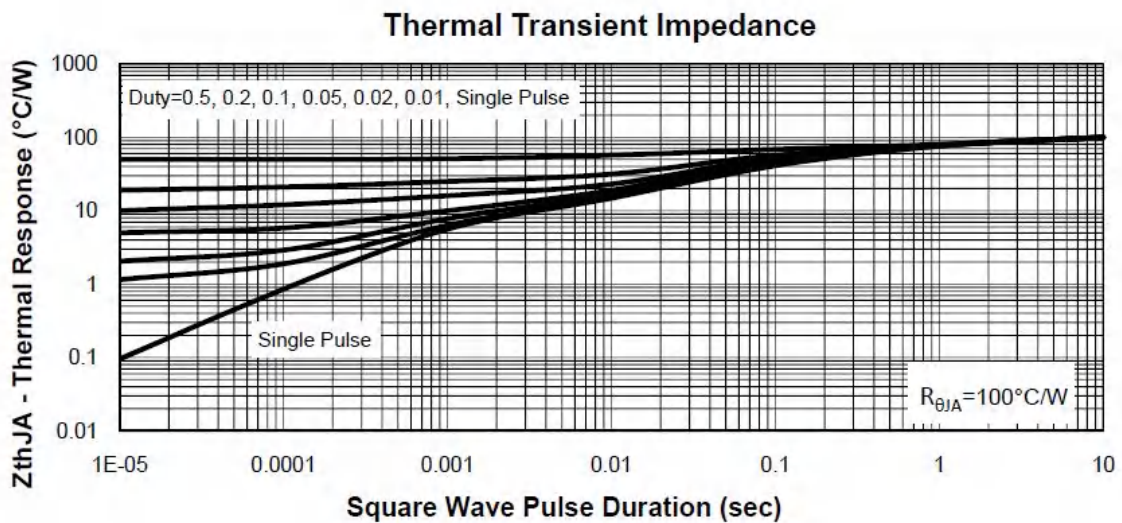
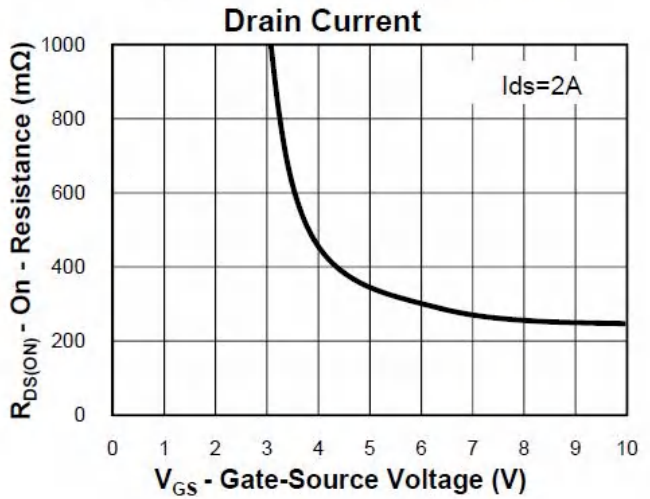
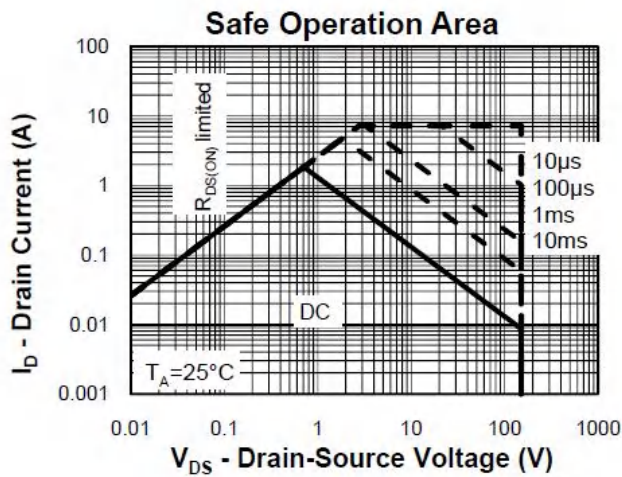
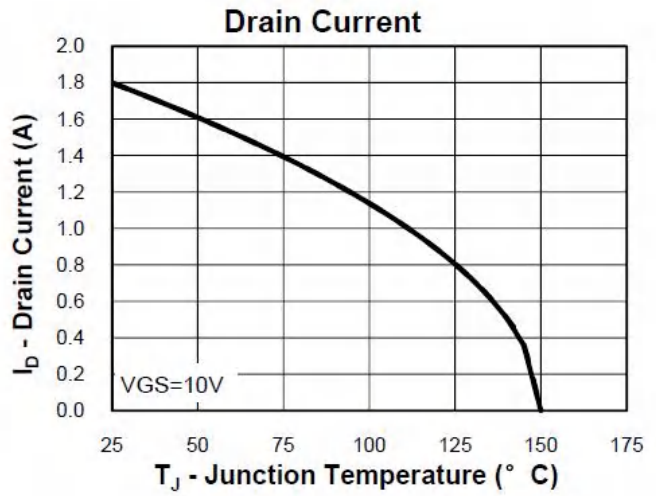
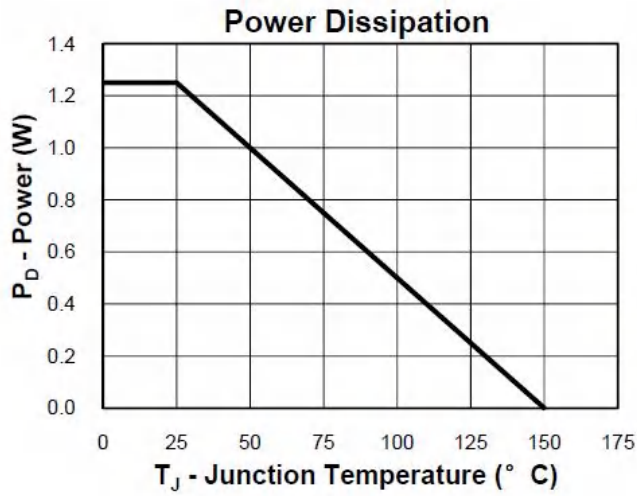
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	1.8	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^\circ\text{C}$	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

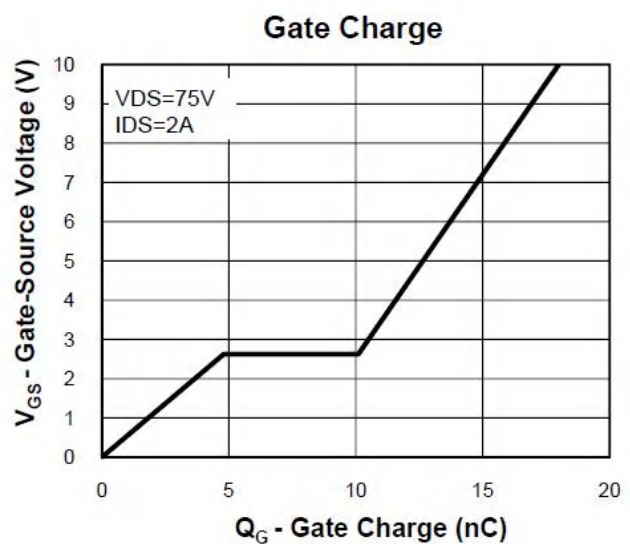
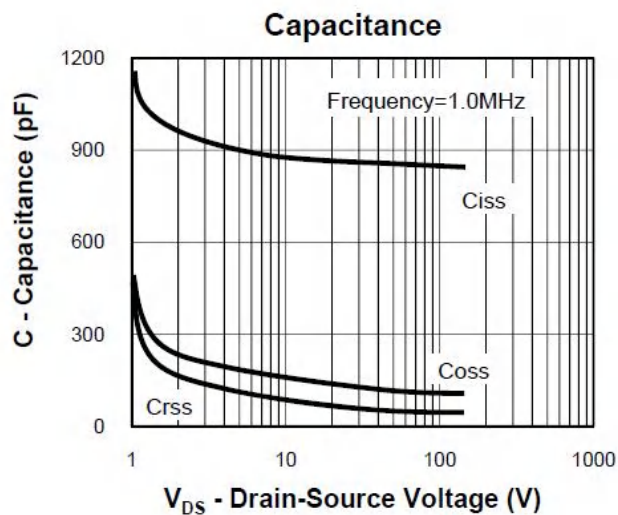
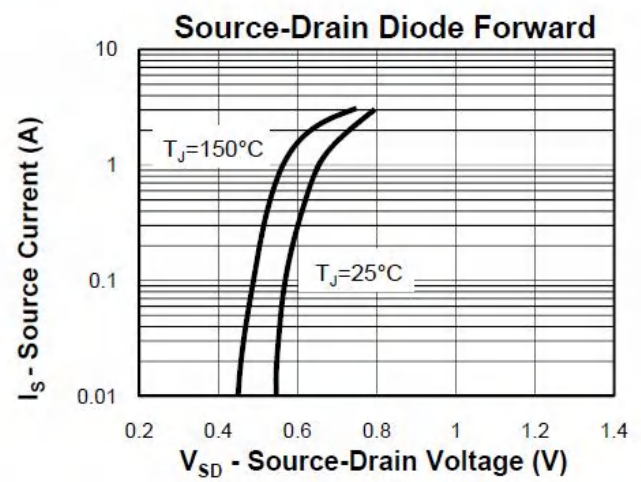
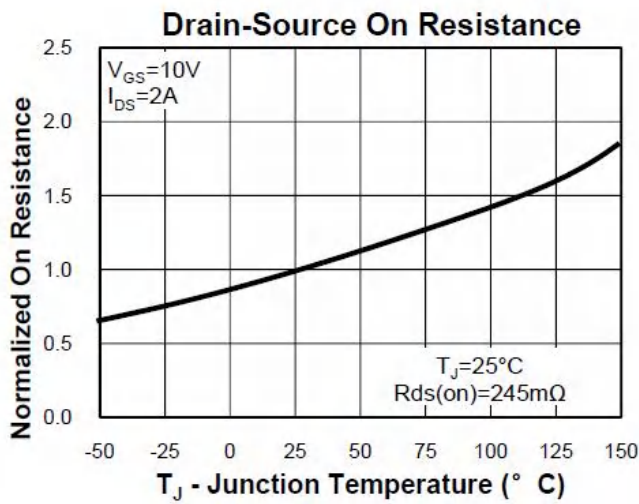
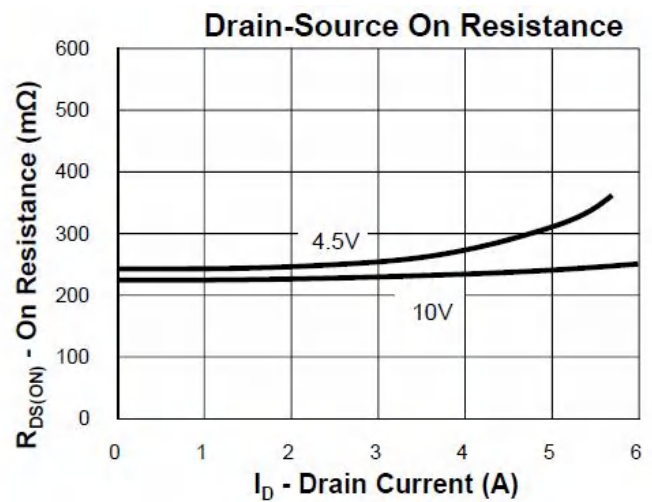
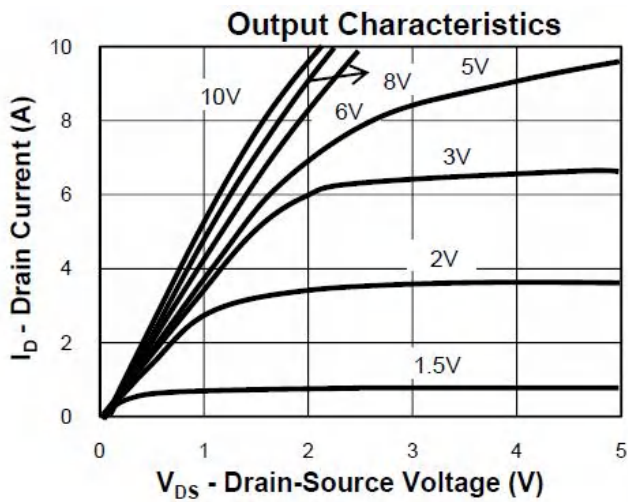


Typical Characteristics





N-Ch 150V Fast Switching MOSFETs

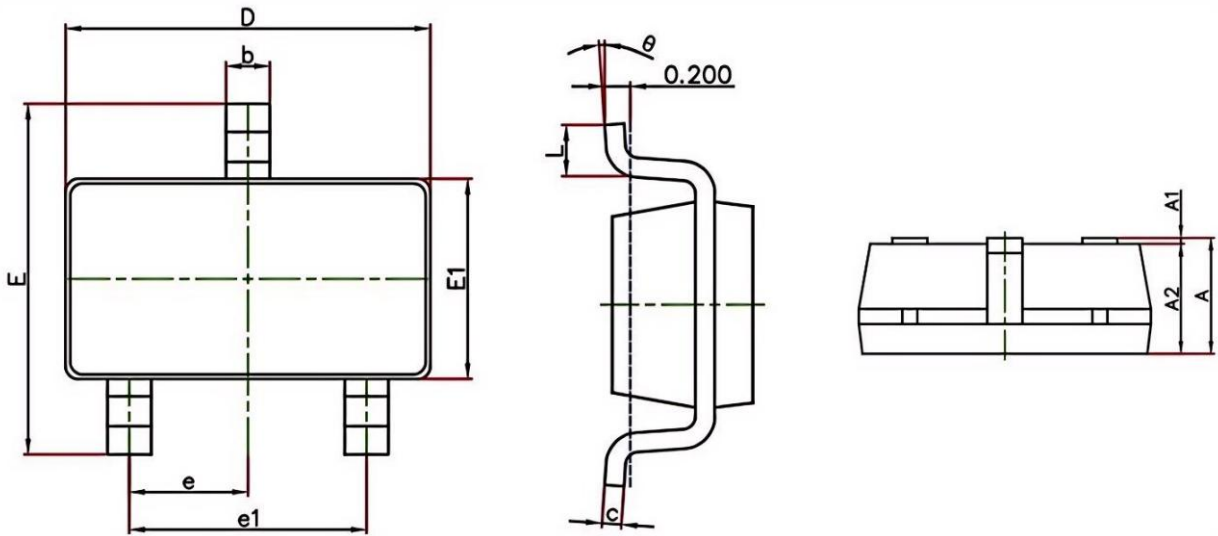




Ordering Information

Part Number	Package code	Packaging
HSS2N15	SOT-23L	3000/Tape&Reel

SOT-23L Package Outline



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
C	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

HSS2N15 TOP Marking

